P-Channel MOS Silicon FET



**CPH3303** 

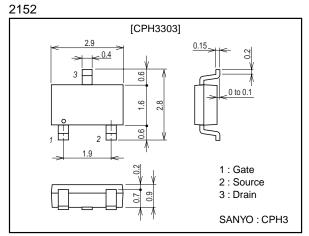
# **Ultrahigh-Speed Switching Applications**

### Features

- · Low ON resistance.
- · Ultrahigh-speed switching.
- $\cdot$  2.5V drive.

## **Package Dimensions**

unit:mm



## **Specifications**

#### Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	ID		-1.6	A
Drain Current (pulse)	IDP	PW≤10µs, duty cycle≤1%	-6.4	A
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0			-10	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.8A	1.6	2.4		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)</sub> 1	I <sub>D</sub> =-0.8A, V <sub>GS</sub> =-4V		245	315	mΩ
	R <sub>DS(on)</sub> 2	I <sub>D</sub> =-0.2A, V <sub>GS</sub> =-2.5V		340	480	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, f=1MHz		180		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		90		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-10V, f=1MHz		43		pF
Marking · IC		•	•	Contin	ued on n	ext page.

Marking : JC

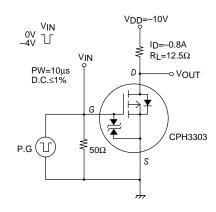
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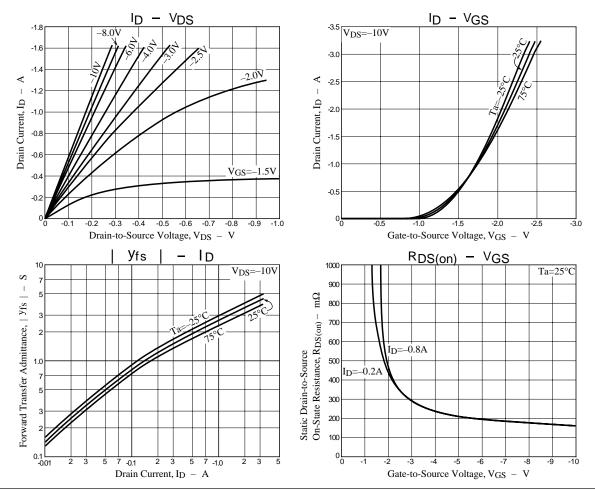
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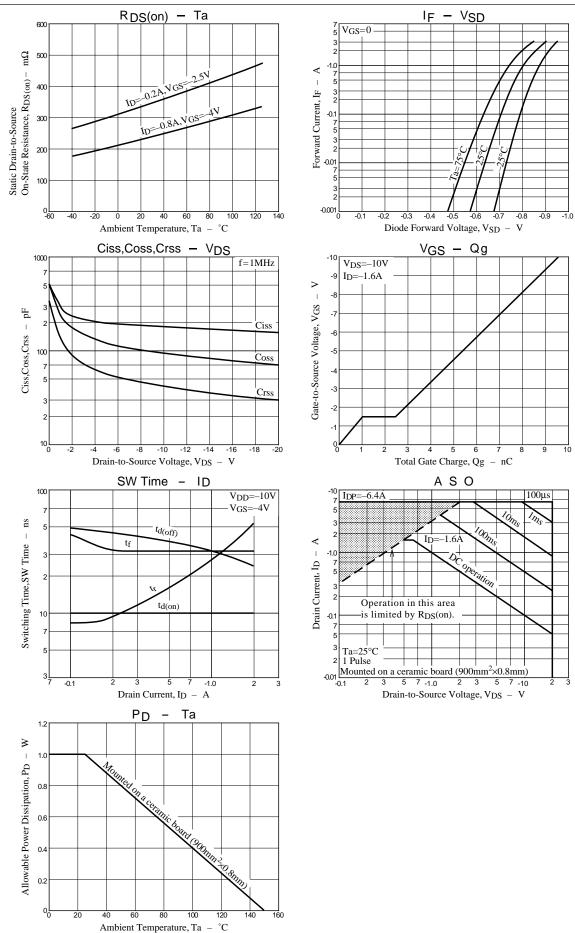
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit		10		ns
Rise Time	tr	See specified Test Circuit		25		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		32		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		32		ns
Total Gate Charge	Qg	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.6A		9.5		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.6A		1		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.6A		1.5		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.6A, V <sub>GS</sub> =0		-1.0	-1.5	V

#### **Switching Time Test Circuit**





No.5988-2/4



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